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Attorney's Docket No. 5308-168

28158  
PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

re: Das et al.

Confirmation No.: 2584

Serial No.: 09/878,442

Group Art Unit: 2815

Filed: June 11, 2001

Examiner: J. Jackson, Jr.

For: HIGH VOLTAGE, HIGH TEMPERATURE CAPACITOR STRUCTURES  
AND METHODS OF FABRICATING SAME

Date: February 26, 2004

Commissioner for Patents  
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PURSUANT TO 37 C.F.R. § 1.97(d)

Sir:

Attached is a list of documents on form PTO-1449 together with a copy of each identified document.

This Information Disclosure Statement is submitted in accordance with 37 C.F.R. § 1.97(c), before final Office Action or Allowance, whichever is earlier.

In accordance with the requirements of 37 C.F.R. § 1.97(c)(2), the \$180.00 fee specified in 37 C.F.R. § 1.17(p) can be charged to Deposit Account No. 50-0220.

This amount is believed to be correct. However, the Commissioner is authorized to charge any deficiency or credit any overpayment to Deposit Account No. 50-0220.

Respectfully submitted,



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LIST OF DOCUMENTS CITED BY APPLICANT

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Applicants: Das et al.

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U. S. PATENT DOCUMENTS

Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date if Appropriate
	1.	5,170,231	12/8/92	Fujii et al.	357	23.2	
	2.	5,885,870A	3/99	Maiti et al.	438	268	
	3.	5,939,763	8/17/99	Hao et al.	257	411	
	4.	5,960,289	9/28/99	Tsui et al.	438	257	
	5.	5,972,801	10/26/99	Lipkin et al.	438	779	
	6.	6,028,012	2/22/00	Wang	438	779	
	7.	6,048,766	4/11/00	Gardner et al.	438	257	
	8.	6,054,352	4/25/00	Ueno	438	268	
	9.	6,063,698	5/16/00	Tseng et al.	438	585	
	10.	6,096,607	8/1/00	Ueno	438	522	
	11.	6,117,735	9/12/00	Ueno	438	268	
	12.	6,136,728	10/24/00	Wang	438	773	
	13.	6,165,822	12/26/00	Okuno et al.	438	142	
	14.	6,190,973 B1	2/20/01	Berg et al.	438	275	
	15.	6,204,203	3/01	Narwanker et al.	438	785	
	16.	6,211,035	4/01	Moise et al.	438	396	
	17.	6,221,700	4/24/01	Okuno et al.	438	151	
	18.	6,239,463	05/29/01	Williams et al.	257	328	
	19.	6,297,172	10/2/01	Kashiwagi	438	773	
	20.	6,455,892	9/24/02	Okuno et al.	257	328	
	21.	6,593,620	07/15/03	Hshieh et al.	257	335	
	22.	6,610,366	08/26/03	Lipkin et al.	427	378	
	23.	US200100558 52A1	12/01	Moise et al.	438	396	
	24.	2002/0072247 A1	6/13/02	Lipkin et al.	438	767	

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<b>FORM PTO-1449</b> U.S. Department of Commerce Patent and Trademark Office				Attorney-Docket Number 5308-168		Serial No. 09/878,442	
LIST OF DOCUMENTS CITED BY APPLICANT (Use several sheets if necessary)				<div style="position: relative; height: 40px;"> <div style="position: absolute; top: -20px; left: 50%; transform: translate(-50%, -50%); font-weight: bold; font-size: 1.2em;">RECEIVED</div> <div style="position: absolute; bottom: -10px; left: 40%; transform: translate(-40%, -50%); font-weight: bold; font-size: 1.1em;">MAR 08 2004</div> </div>			
				Applicants: Das et al.			
				Filing Date: June 11, 2001		Group: 2815	
<b>FOREIGN PATENT DOCUMENTS</b>							
		Document Number	Date	Country	Class	Subclass	Translation Yes   No
	25.	DE 10036208	2/14/02	Germany			Abstract
	26.	DE 198 09 554	9/10/98	Germany			Abstract
	27.	DE 19900171	12/26/00	Germany			Abstract
	28.	JP 03157974	7/5/91	Japan			Abstract
	29.	JP 08264766	10/11/96	Japan			Abstract
	30.	JP 09205202	8/5/97	Japan			Abstract
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	32.	JP 11238742	8/31/99	Japan			Abstract
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	35.	JP 11274487	10/8/99	Japan			Abstract
	36.	JP 2000049167	2/18/00	Japan			Abstract
	37.	JP 2000082812	3/21/00	Japan			Abstract
	38.	JP 2000106371	4/11/01	Japan			Abstract
	39.	JP02000252461A	9/14/00	Japan			Abstract
<b>OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)</b>							
	40.	A.K. Agarwal, J.B. Casady, L.B. Rowland, W.F. Valek, and C.D. Brandt, "1400 V 4H-SiC Power MOSFET's," <i>Materials Science Forum</i> Vols. 264-268, pp.989-992, 1998.					
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62.	K. Ueno and Tadaaki Oikawa, "Counter-Doped MOSFET's of 4H-SiC." <i>IEEE Electron Device Letters</i> ,		

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LIST OF DOCUMENTS CITED BY APPLICANT (Use several sheets if necessary)		Applicants: Das et al;	
Filing Date: June 11, 2001		Group: 2815	
Vol. 20, No. 12, pp. 624-626, December 1999.			
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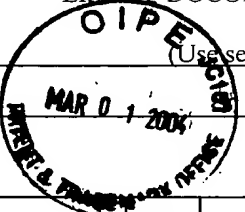
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